

# Specification

## 660nm 200mW Laser Diode

### ■ Features & Applications

- Pulse light output power 340mW
- Maximum operating temperature of 75°C
- Industrial applications

### Absolute Maximum Ratings (T=25°C)

Parameter	Symbol	Unit	Min.	Max.	Note
Optical Power	P <sub>o</sub>	mW		340	Pulse *
				200	CW
LD Reverse voltage	V <sub>R-LD</sub>	V		2	
Operating temperature	T <sub>op</sub>	°C	-10	75	
Storage temperature	T <sub>stg</sub>	°C	-40	100	

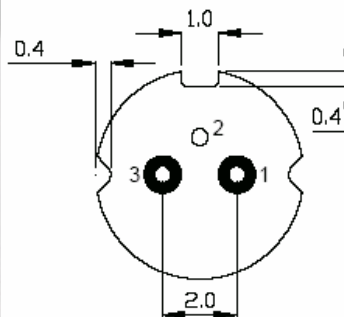
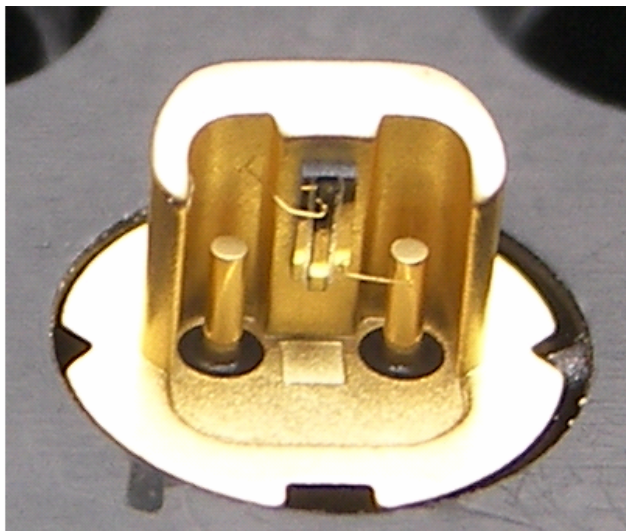
\* Duty cycle less than 35%, pulse width less than 30ns.

### Electro-Optical Characteristics (T=25°C, unless noted otherwise):

Parameter	Symbol	Unit	Min.	Typ	Max.	Test Condition
Threshold Current	I <sub>th</sub>	mA		65		CW
Operating Current	I <sub>op</sub>	mA		250	300	CW, P <sub>o</sub> =200mW
Operating Voltage	V <sub>op</sub>	V		2.4	3.0	CW, P <sub>o</sub> =200mW
Differential efficiency		mW/mA		0.9		CW, P <sub>o</sub> =200mW
Parallel Divergence Angle	//	deg	7	9.5	12	CW, P <sub>o</sub> =200mW
Perpendicular Divergence Angle		deg	14	17	20	CW, P <sub>o</sub> =200mW
Peak Emission Wavelength		nm	650	658	662	CW, P <sub>o</sub> =200mW

\*  $\theta_{//}$  and  $\perp$  are defined as the angle within which the intensity is 50% of the peak value.

### outline Dimensions & Pinout (unit: mm)



Pinout:  
 1 NC  
 2 LD-  
 3 LD+